Abstracts

Internally Matched (IM) Plated Source Bridge (PSB) Power GaAs FET Achieving a High Performance Power Amplifier in X-Band

S. Igi, M. Kobiki, T. Sakayori, M. Ohashi, M. Wataze, T. Suzuki and K. Kusunoki. "Internally Matched (IM) Plated Source Bridge (PSB) Power GaAs FET Achieving a High Performance Power Amplifier in X-Band." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 153-155.

Internal matched devices with 2W and 5W power output at 10 GHz have been developed by using up-side-down mounted GaAs FETs which have PSB (Plated Source Bridge) structures. By parallel running two 5W devices, 7W solid-state power amplifiers in X-band have been practical.

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